

Substitute for form 1449A/B/PTO				Complete If Known	
				Application Number	10/663,741
				Filing Date	September 17, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	2811
				Examiner Name	Not Yet Assigned
Sheet	1	of	3	Attorney Docket Number	M4065.0656/P656

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)	MM-DD-YYYY		
A	US 2004/0035401	2/2004	Ramachandran et al.		
B	US 2003/0212724	11/2003	Ovshinsky et al.		
C	US 2003/0048744	3/2003	Ovshinsky et al.		
D	US 2003/0212725	11/2003	Ovshinsky et al.		
E	US RE 37,259E	7/2001	Ovshinsky		
F	US 3,271,591	9/1966	Ovshinsky		
G	US 3,961,314	6/1976	Klose et al.		
H	US 3,966,317	6/1976	Wacks et al.		
I	US 3,983,542	11/1976	Ovshinsky		
J	US 3,988,720	10/1976	Ovshinsky		
K	US 4,177,474	12/1979	Ovshinsky		
L	US 4,267,261	5/1981	Hallman et al.		
M	US 4,597,162	7/1986	Johnson et al.		
N	US 4,608,296	8/1986	Keem et al.		
O	US 4,637,895	1/1987	Ovshinsky et al.		
P	US 4,646,266	2/1987	Ovshinsky et al.		
Q	US 4,664,939	5/1987	Ovshinsky		
R	US 4,668,968	5/1987	Ovshinsky et al.		
S	US 4,670,763	6/1987	Ovshinsky et al.		
T	US 4,673,957	6/1987	Ovshinsky et al.		
U	US 4,678,679	7/1987	Ovshinsky		
V	US 4,696,758	9/1987	Ovshinsky et al.		
W	US 4,698,234	10/1987	Ovshinsky et al.		
X	US 4,710,899	12/1987	Young et al.		
Y	US 4,728,406	3/1988	Banerjee et al.		
Z	US 4,737,379	4/1988	Hudgens et al.		
A1	US 4,766,471	8/1988	Ovshinsky et al.		
B1	US 4,769,338	9/1988	Ovshinsky et al.		
C1	US 4,775,425	10/1988	Guha et al.		
D1	US 4,788,594	11/1988	Ovshinsky et al.		
E1	US 4,809,044	2/1989	Pryor et al.		
F1	US 4,818,717	4/1989	Johnson et al.		
G1	US 4,843,443	6/1989	Ovshinsky et al.		
H1	US 4,845,533	7/1989	Pryor et al.		
I1	US 4,853,785	8/1989	Ovshinsky et al.		
J1	US 4,891,330	1/1990	Guha et al.		
K1	US 5,128,099	7/1992	Strand et al.		
L1	US 5,159,661	10/1992	Ovshinsky et al.		
M1	US 5,166,758	11/1992	Ovshinsky et al.		
N1	US 5,177,567	1/1993	Klersy et al.		
O1	US 5,296,716	3/1994	Ovshinsky et al.		
P1	US 5,335,219	8/1994	Ovshinsky et al.		
Q1	US 5,359,205	10/1994	Ovshinsky		
R1	US 5,341,328	8/1994	Ovshinsky et al.		
S1	US 5,406,509	4/1995	Ovshinsky et al.		

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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Complete If Known	
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T1	US 5,414,271	5/1995	Ovshinsky et al.	
U1	US 5,534,711	7/1996	Ovshinsky et al.	
V1	US 5,534,712	7/1996	Ovshinsky et al.	
W1	US 5,536,947	7/1996	Klersy et al.	
X1	US 5,543,737	8/1996	Ovshinsky	
Y1	US 5,591,501	1/1997	Ovshinsky et al.	
Z1	US 5,596,522	1/1997	Ovshinsky et al.	
A2	US 5,687,112	11/1997	Ovshinsky	
B2	US 5,694,054	12/1997	Ovshinsky et al.	
C2	US 5,714,768	2/1998	Ovshinsky et al.	
D2	US 5,825,046	10/1998	Czubatyj et al.	
E2	US 5,912,839	6/1999	Ovshinsky et al.	
F2	US 5,933,365	8/1999	Klersy et al.	
G2	US 6,011,757	1/2000	Ovshinsky	
H2	US 6,087,674	7/2000	Ovshinsky et al.	
I2	US 6,141,241	10/2000	Ovshinsky et al.	
J2	US 6,339,544	1/2002	Chlang et al.	
K2	US 6,404,665	6/2002	Lowery et al.	
L2	US 6,429,064	8/2002	Wicker	
M2	US 6,437,383	8/2002	Xu	
N2	US 6,462,984	10/2002	Xu et al.	
O2	US 6,480,438	11/2002	Park	
P2	US 6,487,113	11/2002	Park et al.	
Q2	US 6,501,111	12/2002	Lowery	
R2	US 6,507,061	1/2003	Hudgens et al.	
S2	US 6,511,862	1/2003	Hudgens et al.	
T2	US 6,511,867	1/2003	Lowery et al.	
U2	US 6,512,241	1/2003	Lai	
V2	US 6,514,805	2/2003	Xu et al.	
W2	US 6,531,373	3/2003	Gill et al.	
X2	US 6,534,781	3/2003	Dennison	
Y2	US 6,545,287	4/2003	Chiang	
Z2	US 6,545,907	4/2003	Lowery et al.	
A3	US 6,555,860	4/2003	Lowery et al.	
B3	US 6,563,164	5/2003	Lowery et al.	
C3	US 6,566,700	5/2003	Xu	
D3	US 6,567,293	5/2003	Lowery et al.	
E3	US 6,569,705	5/2003	Chiang et al.	
F3	US 6,570,784	5/2003	Lowery	
G3	US 6,576,921	6/2003	Lowery	
H3	US 6,586,761	7/2003	Lowery	
I3	US 6,589,714	7/2003	Maimon et al.	
J3	US 6,590,807	7/2003	Lowery	
K3	US 6,593,176	7/2003	Dennison	
L3	US 6,597,009	7/2003	Wicker	
M3	US 6,605,527	8/2003	Dennison et al.	
N3	US 6,613,604	9/2003	Maimon et al.	
O3	US 6,621,095	9/2003	Chlang et al.	
P3	US 6,625,054	9/2003	Lowery et al.	
Q3	US 6,642,102	11/2003	Xu	

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R3	US 6,646,297	11/2003	Dennison	
S3	US 6,649,928	11/2003	Dennison	
T3	US 6,667,900	12/2003	Lowery et al.	
U3	US 6,671,710	12/2003	Ovshinsky et al.	
V3	US 6,673,700	1/2004	Dennison et al.	
W3	US 6,674,115	1/2004	Hudgens et al.	
X3	US 6,687,427	2/2004	Ramalingam et al.	
Y3	US 6,690,026	2/2004	Peterson	
Z3	US 6,696,355	2/2004	Dennison	
A4	US 6,687,153	2/2004	Lowery	
B4	US 6,707,712	3/2004	Lowery	
C4	US 6,714,954	3/2004	Ovshinsky et al.	

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		Country Code ² -Number ³ -Kind Code ⁴ (if known)			
					T ⁵

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PTO/SB/08a/b (08-03)

Approved for use through 07/31/2008. OMB 0651-0031

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U.S. PATENT DOCUMENTS					
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FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			
	CA	YOJI KAWAMOTO et al., "Ionic Conduction in As ₂ S ₃ -Ag ₂ S, GeS ₂ -GeS ₂ -GeS-Ag ₂ S and P ₂ S ₅ -Ag ₂ S Glasses," Journal of Non-Crystalline Solids 20 (1976) 393-404.			

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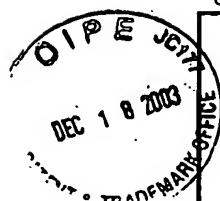
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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	2002/0000666	1/3/2002	Kozicki et al.	
	AB	2002/0072188	6/13/2002	Gilton	
	AC	2002/0106849	08/08/2002	Moore	
	AH	2002/0123169	09/05/2002	Moore et al.	
	AI	2002/0123170	09/05/2002	Moore et al.	
	AJ	2002/0123248	09/05/2002	Moore et al.	
	AK	2002/0127886	09/12/2002	Moore et al.	
	AL	2002/0132417	09/09/2002	Li	
	AF	2002/0160551	10/31/2002	Harshfield	
	AG	2002/0163828	11/07/2002	Krieger et al.	
	AM	2002/0168820	11/2002	Kozicki	
	AN	2002/0168852	11/14/2002	Harshfield et al.	
	AO	2002/0190289	12/19/2002	Harshfield et al.	
	AP	2002/0190350	12/19/2002	Kozicki et al.	
	AQ	2003/0001229	01/02/2003	Moore et al.	
	AR	2003/0027416	02/06/2003	Moore	
	AS	2003/0032254	02/13/2003	Gilton	
	AT	2003/0035314	02/20/2003	Kozicki	
	AU	2003/0035315	02/20/2003	Kozicki	
	AV	2003/0038301	02/27/2003	Moore	
	AW	2003/0043631	03/06/2003	Gilton et al.	
	AX	2003/0045049	03/06/2003	Campbell et al.	
	AY	2003/0045054	03/06/2003	Campbell et al.	
	AZ	2003/0047765	03/13/2003	Campbell	
	AA1	2003/0047772	03/13/2003	Li	
	AB1	2003/0047773	03/13/2003	Li	
	AC1	2003/0048519	03/13/2003	Kozicki	
	AD1	2003/0049912	03/13/2003	Campbell et al.	
	AE1	2003/0068861	04/10/2003	Li	
	AF1	2003/0068862	04/10/2003	Li	
	AG1	2003/0095426	05/22/2003	Hush et al.	
	AH1	2003/0096497	05/22/2003	Moore et al.	
	AI1	2003/0107105	06/12/2003	Kozicki	
	AJ1	2003/0117831	06/26/2003	Hush	
	AK1	2003/0128612	07/10/2003	Moore et al.	
	AL1	2003/0137869	07/24/2003	Kozicki	
	AM1	2003/0143782	07/31/2003	Gilton et al.	
	AN1	2003/0155589	08/21/2003	Campbell et al.	
	AO1	2003/0155606	08/21/2003	Campbell et al.	
	AP1	2003/0156447	08/21/2003	Kozicki	
	AQ1	2003/0156463	08/21/2003	Casper et al.	
	AR1	3,622,319	11/1971	Sharp	
	AS1	3,743,847	7/1973	Boland	
	AT1	4,269,935	5/1981	Masters et al.	

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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

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		Application Number	10/663,741		
		Filing Date	September 17, 2003		
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		Art Unit	N/A		
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Sheet	2	of	11	Attorney Docket Number	M4065.0656/P656

AU1	4,312,938	1/1982	Drexler, et al.	
AV1	4,316,946	1/1982	Masters, et al.	
AW1	4,320,191	3/1982	Yoshikawa et al.	
AX1	4,405,710	9/1983	Balasubramanyam et al.	
AY1	4,419,421	12/1983	Wichelhaus, et al.	
AZ1	4,499,557	2/1985	Holmberg et al.	
AA2	4,671,618	06/09/1987	Wu et al.	
AB2	4,795,657	1/1989	Formigoni et al.	
AC2	4,800,526	01/24/1989	Lewis	
AD2	4,847,674	7/1989	Silwa et al.	
AE2	5,177,567	1/1993	Klersy et al.	
AF2	5,219,788	6/1993	Abernathey et al.	
AG2	5,238,862	8/1993	Bialock et al.	
AH2	5,272,359	12/21/1993	Nagasubramanian et al.	
AI2	5,314,772	5/24/1994	Kozicki	
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AN2	5,512,328	4/1996	Yoshimura et al.	
AO2	5,512,773	4/1996	Wolf et al.	
AP2	5,726,083	3/1998	Takaishi	
AQ2	5,751,012	5/12/1998	Wolstenholme et al.	
AR2	5,761,115	6/1998	Kozicki et al.	
AS2	5,789,277	8/1998	Zahorik et al.	
AT2	5,814,527	9/29/1998	Wolstenholme et al.	
AU2	5,818,749	10/06/1998	Harshfield	
AV2	5,841,150	11/1998	Gonzalez et al.	
AW2	5,846,889	12/1998	Harbison et al.	
AX2	5,851,882	12/22/1998	Harshfield	
AY2	5,869,843	2/9/1999	Harshfield	
AZ2	5,896,312	4/20/1999	Kozicki et al.	
AA3	5,914,893	6/22/1999	Kozicki et al.	
AB3	5,920,788	7/1999	Reinberg	
AC3	5,998,066	12/1999	Block et al.	
AD3	6,031,287	2/29/2000	Harshfield	
AE3	6,072,716	06/06/2000	Jacobson et al.	
AF3	6,077,729	6/2000	Harshfield	
AG3	6,084,796	7/4/2000	Kozicki et al.	
AH3	6,177,338	1/2001	Liaw et al.	
AI3	6,117,720	9/2000	Harshfield	
AJ3	6,143,604	11/2000	Chiang et al.	
AK3	6,236,059	5/2001	Wolstenholme et al.	
AL3	6,297,170	10/2001	Gabriel et al.	
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AO3	6,329,606	12/2001	Freyman et al.	
AP3	6,348,365	2/19/2002	Moore et al.	
AQ3	6,350,679	2/2002	McDaniel et al.	

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AR3	6,376,284	4/2002	Gonzalez et al.	
AS3	6,388,324	5/14/2002	Kozicki et al.	
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AU3	6,414,376	7/2002	Thakur et al.	
AV3	6,418,049	7/9/2002	Kozicki et al.	
AW3	6,420,725	7/16/2002	Harshfield	
AX3	6,423,628	7/2002	Li et al.	
AY3	6,440,837	8/27/2002	Harshfield	
AZ3	6,469,364	10/2002	Kozicki	
AA4	6,473,332	10/2002	Ignatiev et al.	
AB4	6,487,106	11/26/2002	Kozicki	
AC4	2003/0209728	11/13/2003	Kozicki et al	
AD4	2003/0209971	11/13/2003	Kozicki et al	
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AF4	2002/0101765	08/01/2002	Mihnea et al.	
AG4	6,426,898	07/30/2002	Mihnea et al.	
AH4	2002/0130351	09/19/2002	Ghodsi	
AI4	2002/0159292	10/31/2002	Forbes	
AJ4	5,534,712	07/09/1996	Ovshinsky et al.	
AK4	2002/0163030	11/07/2002	Mandell et al.	
AL4	2002/0094640	07/18/2002	Forbes	
AM4	2002/0126533	09/12/2002	Kao	

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BA	56126916		10/19981	Akira et al.		
BB	WO 97/48032		12/18/1997	Kozicki et al.		
BC	WO 99/28914		06/10/1999	Kozicki et al.		
BD	WO 00/48196		08/17/2000	Kozicki et al.		
BE	WO 02/21542		03/14/2002	Kozicki et al.		

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	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.			
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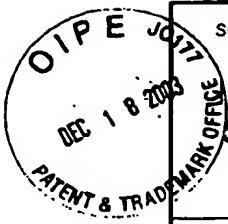
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 INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				C omplete if Known	
				Application Number	10/663,741
				Filing Date	September 17, 2003
				First Named Inventor	Terry L. Gilton
				Group Art Unit	N/A
				Examiner Name	Not Yet Assigned
Sheet	6	of	11	Attorney Docket Number	M4065.0656/P656

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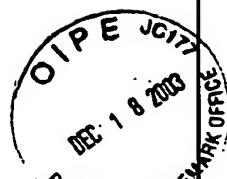
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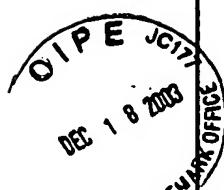
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